

**Thyristors  
logic level**

**BT258U series**

**GENERAL DESCRIPTION**

Passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

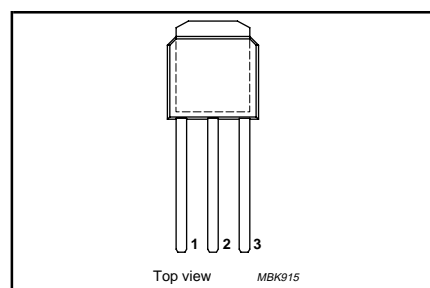
**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
$V_{DRM}$ , $V_{RRM}$	<b>BT258U-</b> Repetitive peak off-state voltages	<b>500R</b> 500	<b>600R</b> 600	<b>800R</b> 800	V
$I_{T(AV)}$		5	5	5	A
$I_{T(RMS)}$		8	8	8	A
$I_{TSM}$	Non-repetitive peak on-state current	75	75	75	A

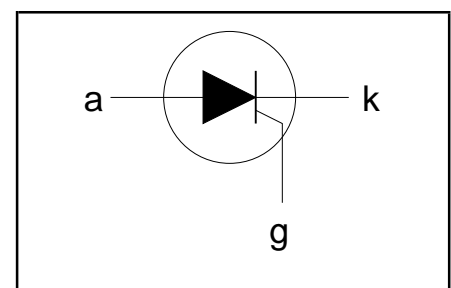
**PINNING - SOT533**

PIN NUMBER	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

**PIN CONFIGURATION**



**SYMBOL**



**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500R 500 <sup>1</sup>	-600R 600 <sup>1</sup>	-800R 800	
$V_{DRM}$ , $V_{RRM}$	Repetitive peak off-state voltages		-				V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{mb} \leq 111\text{ °C}$	-	5			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	8			A
$I_{TSM}$	Non-repetitive peak on-state current	half sine wave; $T_j = 25\text{ °C}$ prior to surge $t = 10\text{ ms}$	-	75			A
$I^2t$	$I^2t$ for fusing	$t = 8.3\text{ ms}$	-	82			A
$dl_T/dt$	Repetitive rate of rise of on-state current after triggering	$t = 10\text{ ms}$ $I_{TM} = 10\text{ A}$ ; $I_G = 50\text{ mA}$ ; $dl_G/dt = 50\text{ mA}/\mu\text{s}$	-	28			A <sup>2</sup> s
$I_{GM}$	Peak gate current		-	50			A/ $\mu\text{s}$
$V_{GM}$	Peak gate voltage		-	2			A
$V_{RGM}$	Peak reverse gate voltage		-	5			V
$P_{GM}$	Peak gate power		-	5			W
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	0.5			W
$T_{stg}$	Storage temperature		-40	150			°C
$T_j$	Operating junction temperature		-	125 <sup>2</sup>			°C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu\text{s}$ .

2 Note: Operation above 110°C may require the use of a gate to cathode resistor of 1k $\Omega$  or less.

Thyristors  
logic level

## BT258U series

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	in free air	-	-	2.0	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		-	70	-	K/W

## STATIC CHARACTERISTICS

 $T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{GT}$	Gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	50	200	$\mu\text{A}$
$I_L$	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	0.4	10	mA
$I_H$	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	0.3	6	mA
$V_T$	On-state voltage	$I_T = 16\text{ A}$	-	1.3	1.5	V
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	-	0.4	1.5	V
$I_D, I_R$	Off-state leakage current	$V_D = V_{DRM(max)}; I_T = 0.1\text{ A}; T_j = 110\text{ °C}$	0.1	0.2	-	V
		$V_D = V_{DRM(max)}; V_R = V_{RRM(max)}; T_j = 125\text{ °C}$	-	0.1	0.5	mA

## DYNAMIC CHARACTERISTICS

 $T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ exponential waveform; $R_{GK} = 100\ \Omega$	50	100	-	V/ $\mu\text{s}$
$t_{gt}$	Gate controlled turn-on time	$I_{TM} = 10\text{ A}; V_D = V_{DRM(max)}; I_G = 5\text{ mA};$ $dI_G/dt = 0.2\text{ A}/\mu\text{s}$	-	2	-	$\mu\text{s}$
$t_q$	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}; T_j = 125\text{ °C};$ $I_{TM} = 12\text{ A}; V_R = 24\text{ V}; dI_{TM}/dt = 10\text{ A}/\mu\text{s};$ $dV_D/dt = 2\text{ V}/\mu\text{s}; R_{GK} = 1\text{ k}\Omega$	-	100	-	$\mu\text{s}$

Thyristors  
logic level

BT258U series

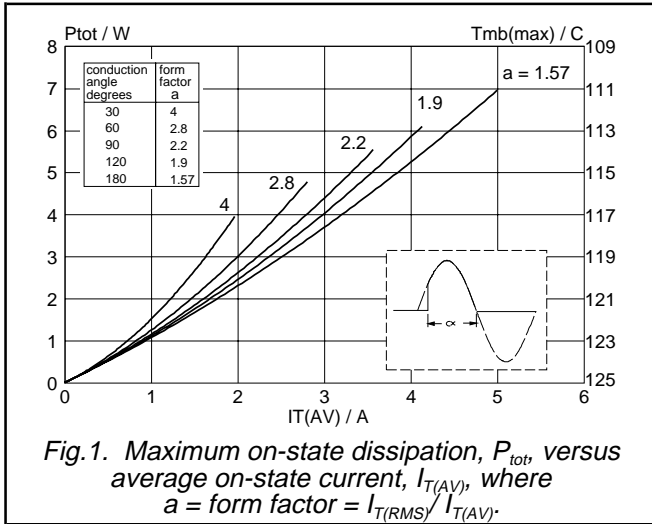


Fig. 1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = \text{form factor} = I_{T(RMS)} / I_{T(AV)}$ .

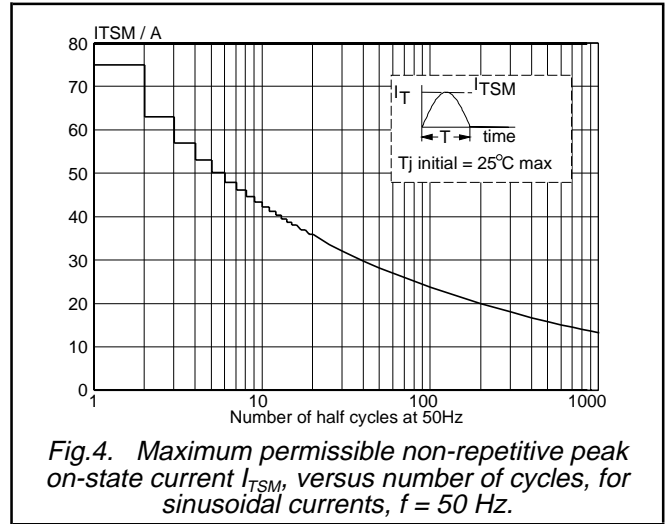


Fig. 4. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50 \text{ Hz}$ .

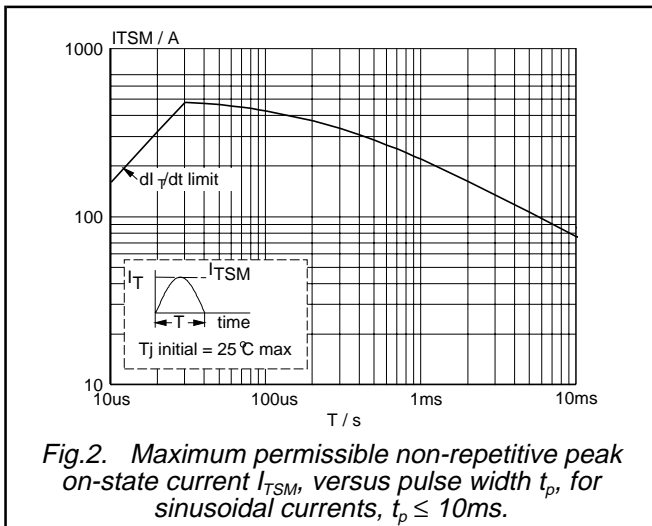


Fig. 2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 10 \text{ ms}$ .

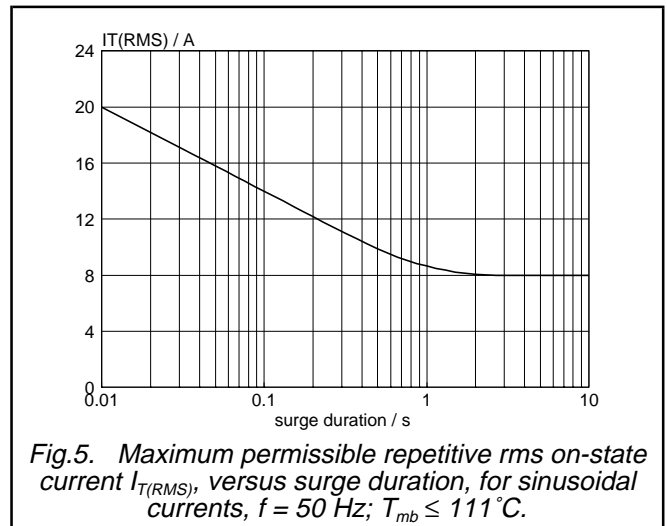


Fig. 5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50 \text{ Hz}$ ;  $T_{mb} \leq 111^\circ \text{C}$ .

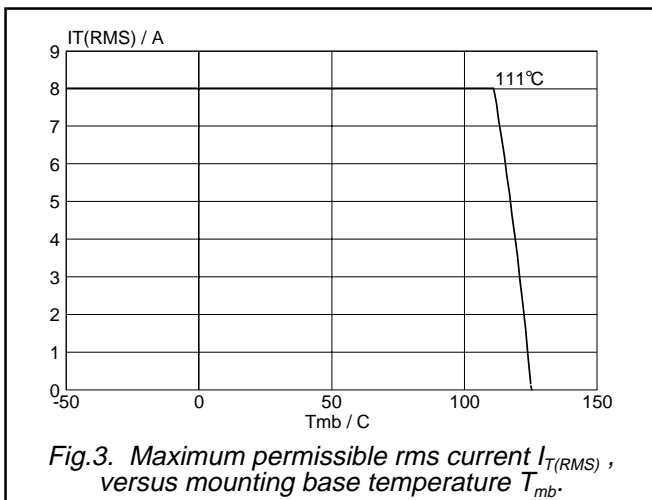


Fig. 3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

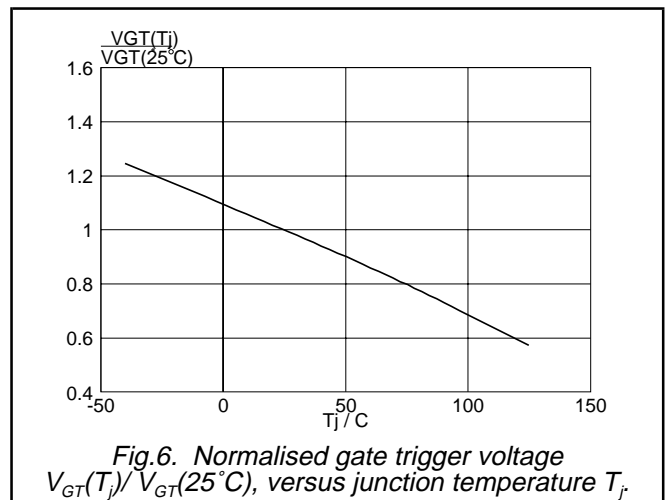
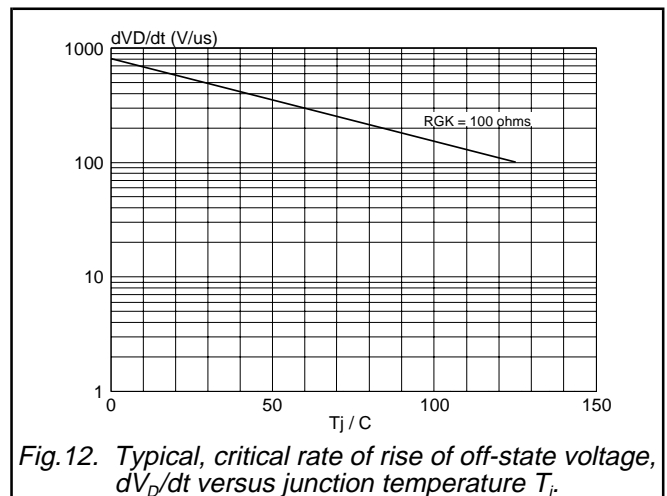
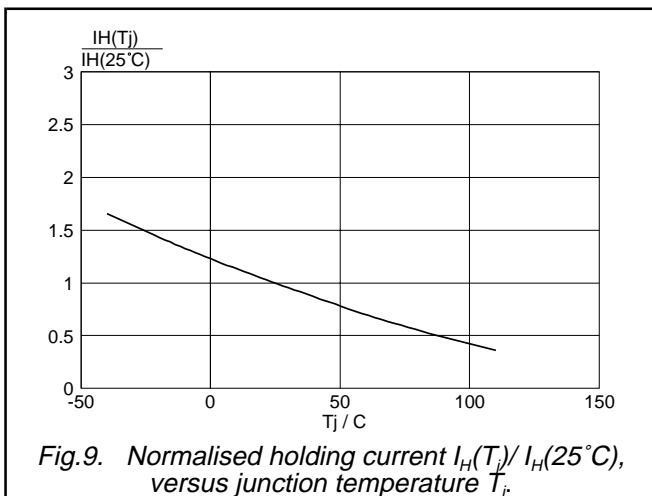
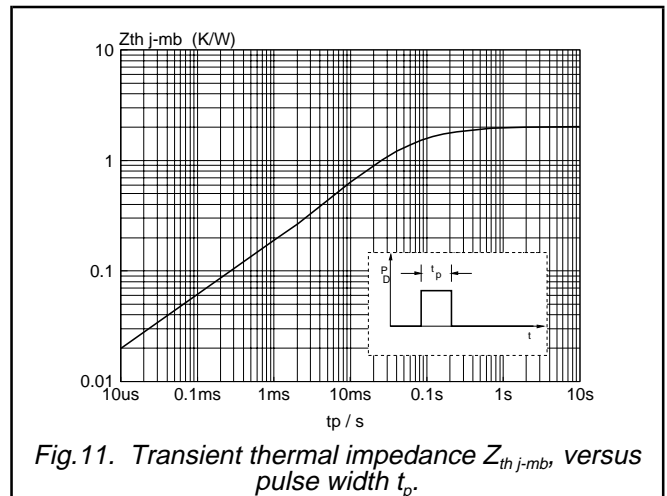
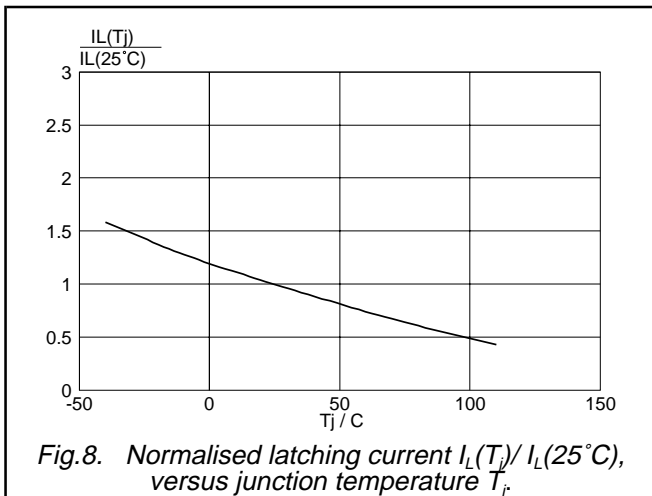
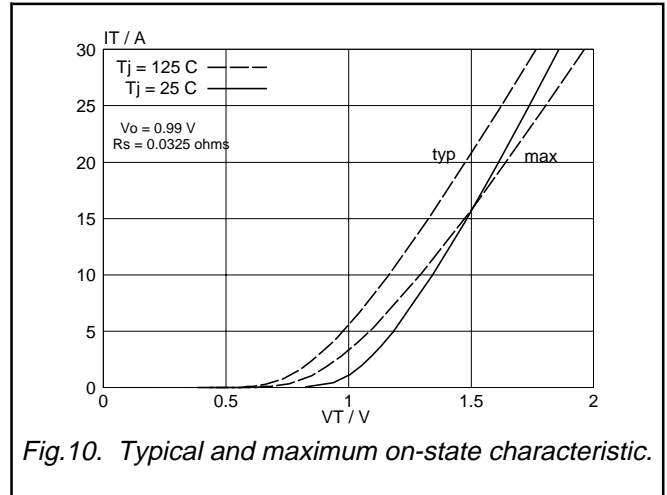
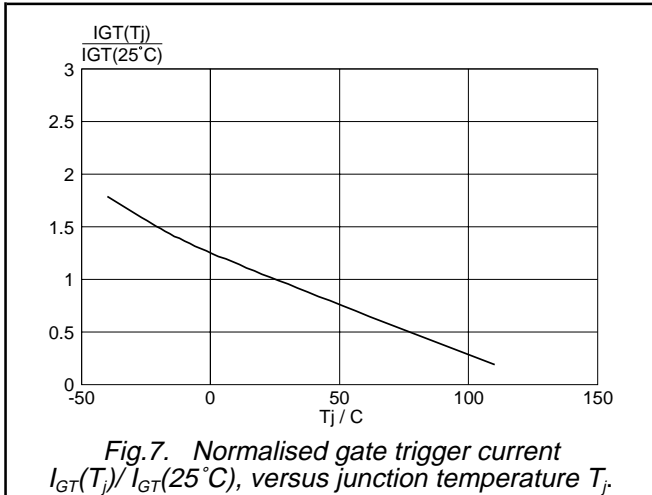


Fig. 6. Normalised gate trigger voltage  $V_{GT}(T_j) / V_{GT}(25^\circ \text{C})$ , versus junction temperature  $T_j$ .

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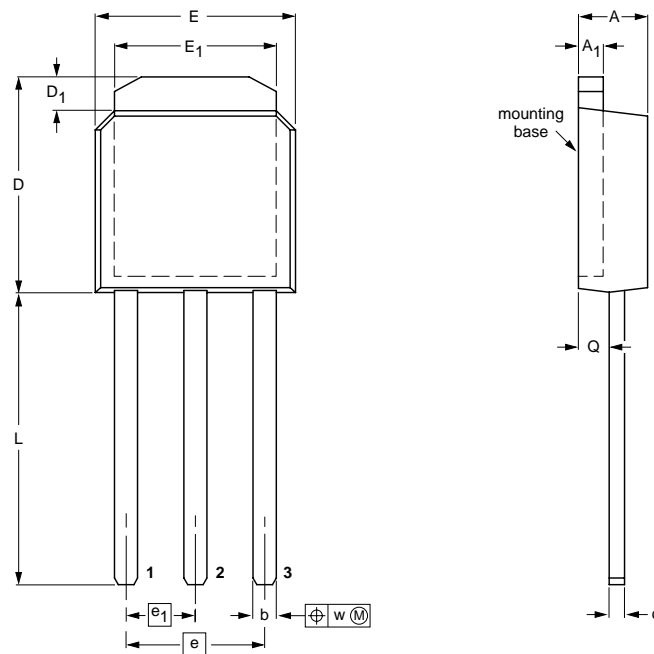
BT258U series

**MECHANICAL DATA**

Dimensions in mm Net Mass: 1.3 g

Plastic single-ended package (Philips version of I-PAK); 3 leads (in-line)

SOT533



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	c	D	D <sub>1</sub>	E	E <sub>1</sub>	e	e <sub>1</sub>	L	Q
mm	2.38 2.22	0.89 0.71	0.89 0.71	0.56 0.46	7.28 6.94	1.06 0.96	6.73 6.47	5.36 5.26	4.57	2.285	9.8 9.4	1.00 1.10

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT533		TO-251			99-02-18

Fig.13. SOT533 (TO251). pin 2 connected to mounting base.

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**BT258U series****DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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